



STW27NM60ND Information



For Reference Only

Part Number STW27NM60ND
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 21A TO-247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STW27NM60ND Specifications

Manufacturer Part NumberSTW27NM60NDManufacturerSTMicroelectronicsCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-247-3SeriesFDmesh? IIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C21A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series FDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds	Manufacturer Part Number	STW27NM60ND
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Package TO-247-3 Series FDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds -	Category	Discrete Semiconductor Products
SeriesFDmesh? IIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C21A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds N-Channel NOSFET (Metal Oxide) 500V 21A (Tc) 51V 52V @ 250μA 53V @ 250μA -	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds MOSFET (Metal Oxide) 500 21A (Tc) 10V 5V @ 250μA -	Series	FDmesh? II
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 21A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 600V 21A (Tc) 51V 51V 52D 51V 52D 51V 52D 52D 52D 52D 52D 52D 52D 52	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 21A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds -	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Stv @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds -	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds -	Current - Continuous Drain (Id) @ 25°C	21A (Tc)
Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds -	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds -	Vgs(th) (Max) @ Id	5V @ 250μA
	Gate Charge (Qg) (Max) @ Vgs	-
Voc (Mov)	Input Capacitance (Ciss) (Max) @ Vds	-
Vgs (Max)	Vgs (Max)	±25V
FET Feature -	FET Feature	-
Power Dissipation (Max) 160W (Tc)	Power Dissipation (Max)	160W (Tc)
Rds On (Max) @ Id, Vgs 160 mOhm @ 10.5A, 10V	Rds On (Max) @ Id, Vgs	160 mOhm @ 10.5A, 10V
Operating Temperature 150°C (TJ)	Operating Temperature	150°C (TJ)
Mounting Type Through Hole	Mounting Type	Through Hole
Supplier Device Package TO-247-3	Supplier Device Package	TO-247-3
Package / Case TO-247-3	Package / Case	TO-247-3
Report errors		Report errors?

STW27NM60ND Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STW27NM60ND Payment Methods





















STW27NM60ND Shipping Methods













If you have any question about STW27NM60ND, please do not hesitate to contact us!

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